

MB81256-10/-12/-15

MOS 262,144 BIT DYNAMIC RANDOM ACCESS MEMORY

262,144 Bit Dynamic Random Access Memory

The Fujitsu MB81256 is a fully decoded, dynamic NMOS random access memory organized as 262,144 one-bit words. The design is optimized for high speed, high performance applications such as mainframe memory, buffer memory, peripheral storage, and environments where low power dissipation and a compact layout are required.

Multiplexed row and column address inputs permit the MB81256 to be housed in standard 16-pin DIP and ZIP packages or an 18-pin PLCC package. Pinouts conform to JEDEC-approved pinouts. Additionally, the MB81256 offers new functional enhancements that make it more versatile than previous dynamic RAMs. CAS-before-RAS refresh provides an on-chip refresh capability that is upwardly compatible with the MB8266A. The MB81256 also features page mode which allows high speed random access of up to 512 bits of data within the same row.

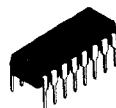
The MB81256 is fabricated using silicon gate NMOS and Fujitsu's advanced Triple-layer Polysilicon process. This process, coupled with single-transistor memory storage cells, permits maximum circuit density and minimal chip size. Dynamic circuitry is used in the design, including the sense amplifiers. Clock timing requirements are noncritical, and power supply tolerance is very wide. All inputs are TTL compatible.

- 262,144 x 1 RAM organization
- Silicon-gate, Triple Poly NMOS, single transistor cell
- Row Access Time
 - 100 ns max. (MB 81256-10)
 - 120 ns max. (MB 81256-12)
 - 150 ns max. (MB 81256-15)
- Cycle Time
 - 200 ns min. (MB 81256-10)
 - 220 ns min. (MB 81256-12)
 - 260 ns min. (MB 81256-15)
- Page Cycle Time
 - 100 ns max. (MB 81256-10)
 - 120 ns max. (MB 81256-12)
 - 145 ns max. (MB 81256-15)
- Single +5 V Supply, $\pm 10\%$ tolerance
- Low Power
 - 385 mW max. (MB 81256-10)
 - 358 mW max. (MB 81256-12)
 - 314 mW max. (MB 81256-15)
 - 25 mW max. (standby)
- 256 refresh cycles every 4 ms
- CAS-before-RAS, RAS-only, Hidden refresh capability
- High speed Read-write cycle
- t_{AR} , t_{WCR} , t_{OHR} , t_{WPD} are eliminated
- Output unlatched cycle end allows two-dimensional chip select
- Common I/O capability using Early Write operation
- On-chip latches for Addresses and Data-in
- Standard 16-Pin Plastic Packages:
 - DIP (MB81256-XXP)
 - ZIP (MB81256-XXPSZ)
- Standard 18-Pin Plastic Package:
 - PLCC (MB81256-XXPV)
- Standard 16-Pin Ceramic Packages:
 - DIP (MB81256-XXC) Seam Weld
 - DIP (MB81256-XXZ) CerDip
- Standard 18-Pad Ceramic Package:
 - LCC (MB81256-XXTV)

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage at any pin relative to V_{SS}	V_{IN} , V_{OUT}	-1 to +7	V
Voltage of V_{CC} supply relative to V_{SS}	V_{CC}	-1 to +7	V
Storage Temperature	Ceramic	T_{STG}	$^{\circ}C$
	Plastic	-55 to +125	
Power Dissipation	P_D	1.0	W
Short Circuit Output Current	—	50	mA

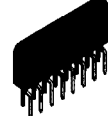
Note: Permanent device damage may occur if absolute maximum ratings are exceeded. Functional operation should be restricted to the conditions as detailed in the operation sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



PLASTIC PACKAGE
DIP-16P-M03



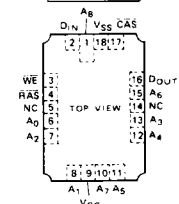
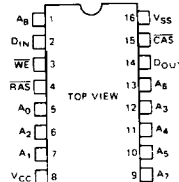
PLASTIC PACKAGE
LCC-18P-M04



PLASTIC PACKAGE
ZIP-16P-M01

DIP-16C-A03: See Page 17
DIP-16C-A04: See Page 18
DIP-16C-C04: See Page 19
LCC-18C-F04: See Page 24

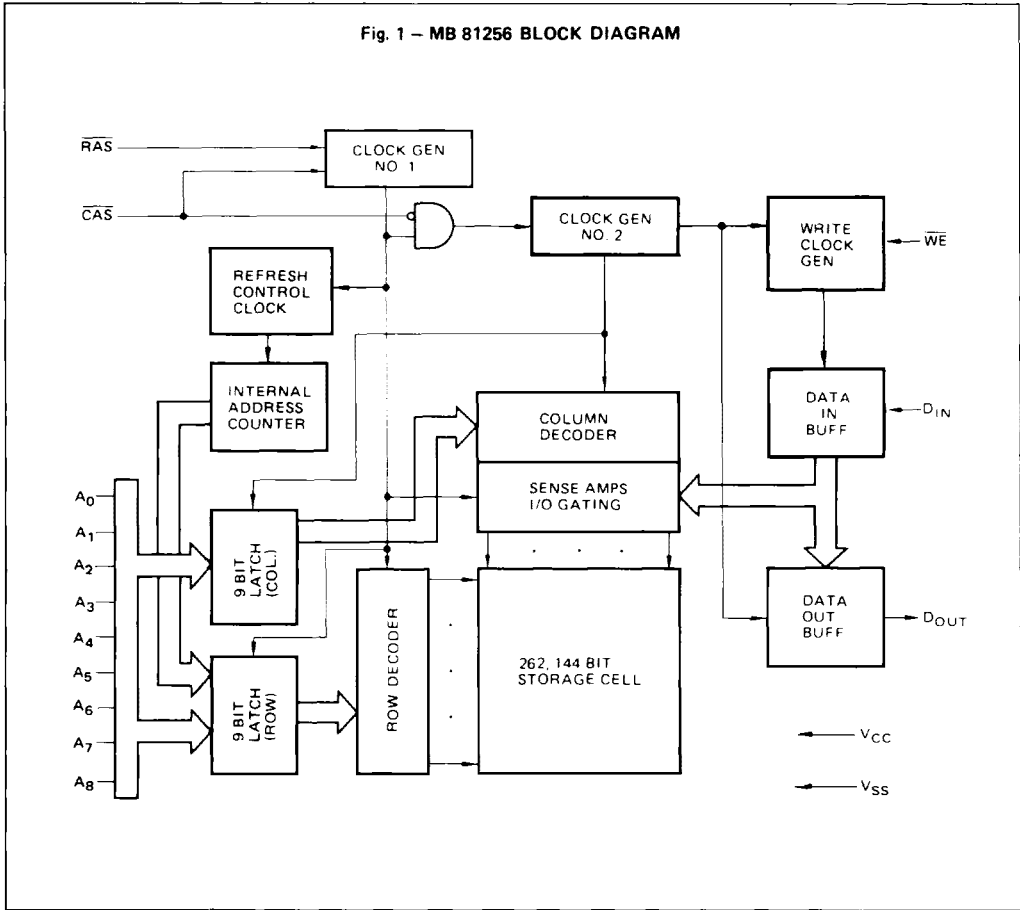
PIN ASSIGNMENT



Pin assignment for ZIP: See Page 21

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

Fig. 1 – MB 81256 BLOCK DIAGRAM



CAPACITANCE ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Typ	Max	Unit
Input Capacitance A_0 to A_8 , D_{IN}	C_{IN1}		7	pF
Input Capacitance $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$	C_{IN2}		10	pF
Output Capacitance D_{OUT}	C_{OUT}		7	pF

RECOMMENDED OPERATING CONDITIONS

(Referenced to V_{SS})

Parameter	Symbol	Min	Typ	Max	Unit	Operating Temperature
Supply Voltage	V_{CC}	4.5	5.0	5.5	V	0°C to +70°C
	V_{SS}	0	0	0	V	
Input High Voltage, all inputs	V_{IH}	2.4		6.5	V	
Input Low Voltage, all inputs	V_{IL}	-2.0		0.8	V	

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DC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
OPERATING CURRENT* Average Power Supply Current (RAS, CAS cycling; t_{RC} = Min.)	MB 81256-10 MB 81256-12 MB 81256-15	I_{CC1}		70	mA
				65	
				57	
STANDBY CURRENT Standby Power Supply Current (RAS, CAS = V_{IH})		I_{CC2}		4.5	mA
REFRESH CURRENT 1* Average Power Supply Current (RAS cycling, CAS = V_{IH} ; t_{RC} = Min.)	MB 81256-10 MB 81256-12 MB 81256-15	I_{CC3}		60	mA
				55	
				50	
PAGE MODE CURRENT* Average Power Supply Current (RAS = V_{IL} , CAS cycling; t_{PC} = Min.)	MB 81256-10 MB 81256-12 MB 81256-15	I_{CC4}		35	mA
				30	
				25	
REFRESH CURRENT 2* Average Power Supply Current (CAS-before-RAS; t_{RC} = Min.)	MB 81256-10 MB 81256-12 MB 81256-15	I_{CC5}		65	mA
				60	
				55	
INPUT LEAKAGE CURRENT any input (V_{IN} = 0V to 5.5V, V_{CC} = 5.5V, V_{SS} = 0V, all other pins not under test = 0V)		$I_{I(L)}$	-10	10	μ A
OUTPUT LEAKAGE CURRENT (Data is disabled, V_{OUT} = 0V to 5.5V)		$I_{O(L)}$	-10	10	μ A
OUTPUT LEVEL Output Low Voltage (I_{OL} = 4.2 mA)		V_{OL}		0.4	V
OUTPUT LEVEL Output high Voltage (I_{OH} = -5.0 mA)		V_{OH}	2.4		V

NOTE * : I_{CC} is depended on output loading and cycle rates. Specified values are obtained with the output open.

AC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.) NOTES 1, 2, 3

Parameter	Symbol	MB 81256-10		MB 81256-12		MB 81256-15		Unit
		Min	Max	Min	Max	Min	Max	
Time between Refresh	t_{REF}		4		4		4	ms
Random Read/Write Cycle Time	t_{RC}	200		220		260		ns
Read-Write Cycle Time	t_{RWC}	200		220		260		ns
Access Time from $\overline{RAS}$	t_{RAC}		100		120		150	ns
Access Time from $\overline{CAS}$	t_{CAC}		50		60		75	ns
Output Buffer Turn off Delay	t_{OFF}	0	25	0	25	0	30	ns
Transition Time	t_T	3	50	3	50	3	50	ns
$\overline{RAS}$ Precharge Time	t_{RP}	85		90		100		ns
$\overline{RAS}$ Pulse Width	t_{RAS}	105	100000	120	100000	150	100000	ns
$\overline{RAS}$ Hold Time	t_{RSH}	55		60		75		ns
$\overline{CAS}$ Pulse Width	t_{CAS}	55	100000	60	100000	75	100000	ns
$\overline{CAS}$ Hold Time	t_{CSH}	105		120		150		ns
$\overline{RAS}$ to $\overline{CAS}$ Delay Time	t_{RCD}	20	50	22	60	25	75	ns
$\overline{CAS}$ to $\overline{RAS}$ Set Up Time	t_{CRS}	10		10		10		ns
Row Address Set Up Time	t_{ASR}	0		0		0		ns
Row Address Hold Time	t_{RAH}	10		12		15		ns
Column Address Set Up Time	t_{ASC}	0		0		0		ns
Column Address Hold Time	t_{CAH}	15		20		25		ns
Read Command Set Up Time	t_{RCS}	0		0		0		ns
Read Command Hold Time Referenced to $\overline{CAS}$	t_{RCH}	0		0		0		ns
Read Command Hold Time Referenced to $\overline{RAS}$	t_{RRH}	20		20		20		ns
Write Command Set Up Time	t_{WCS}	0		0		0		ns
Write Command Pulse Width	t_{WP}	15		20		25		ns
Write Command Hold Time	t_{WCH}	15		20		25		ns
Write Command to $\overline{RAS}$ Lead Time	t_{RWL}	35		40		45		ns
Write Command to $\overline{CAS}$ Lead Time	t_{CWL}	35		40		45		ns
Data In Set Up Time	t_{DS}	0		0		0		ns
Data In Hold Time	t_{DH}	15		20		25		ns
$\overline{CAS}$ to $\overline{WE}$ Delay	t_{CWD}	15		20		25		ns
Refresh Set Up Time for $\overline{CAS}$ Referenced to $\overline{RAS}$ ($\overline{CAS}$ -before- $\overline{RAS}$ cycle)	t_{FCS}	20		20		20		ns
Refresh Hold Time for $\overline{CAS}$ Referenced to $\overline{RAS}$ ($\overline{CAS}$ -before- $\overline{RAS}$ cycle)	t_{FCH}	20		25		30		ns

AC CHARACTERISTICS

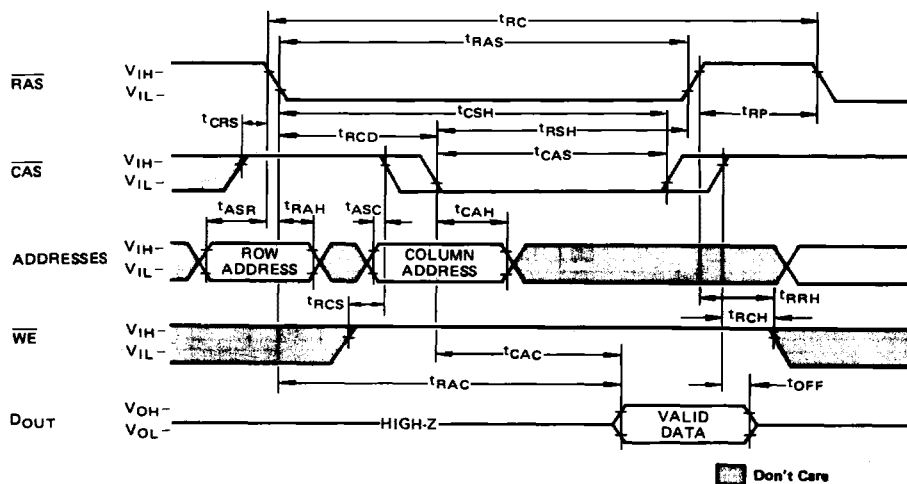
(Recommended operating conditions unless otherwise noted.)

Parameter	Symbol	MB 81256-10		MB 81256-12		MB 81256-15		Unit
		Min	Max	Min	Max	Min	Max	
CAS Precharge Time ($\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ cycle)	t_{CPR}	20		25		30		ns
$\overline{\text{RAS}}$ Precharge to $\overline{\text{CAS}}$ Active Time (Refresh cycles)	t_{RPC}	20		20		20		ns
Page Mode Read/Write Cycle Time	t_{PC}	100		120		145		ns
Page Mode Read-Write Cycle Time	t_{PRWC}	100		120		145		ns
Page Mode $\overline{\text{CAS}}$ Precharge Time	t_{CP}	40		50		60		ns
Refresh Counter Test Cycle Time	t_{RTC}	330		375		430		ns
Refresh Counter Test $\overline{\text{RAS}}$ Pulse Width	t_{TRAS}	230	10000	265	10000	320	10000	ns
Refresh Counter Test $\overline{\text{CAS}}$ Precharge Time	t_{CPT}	50		60		70		ns

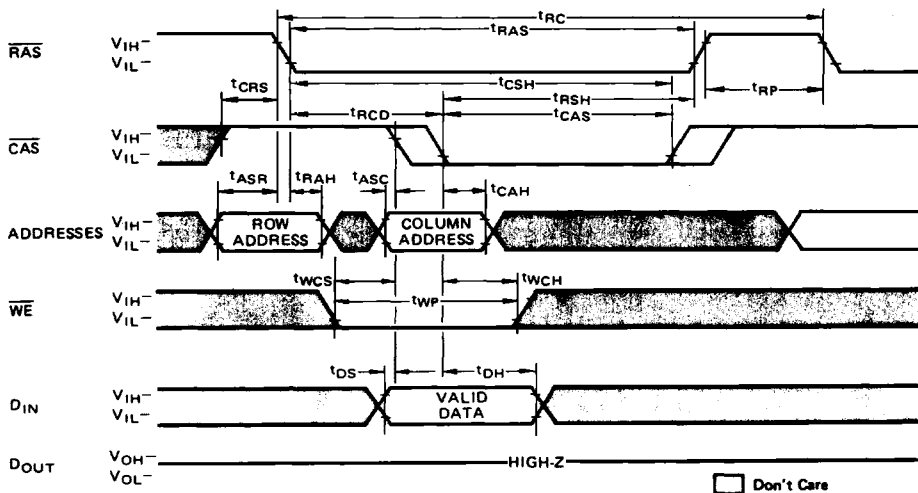
Notes:

- 1 An initial pause of 200 μs is required after power-up. And then several cycle (to which any 8 cycle to perform refresh are adequate) are required before proper device operation is achieved. If internal refresh counter is to be effective, a minimum of 8 $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh cycles are required.
- 2 AC characteristics assume $t_T = 5 \text{ ns}$.
- 3 V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} (min) and V_{IL} (max.).
- 4 Assumes that $t_{\text{RCD}} \leq t_{\text{RCD}} (\text{max.})$. If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAC} will increase by the amount that t_{RCD} exceeds the value shown.
- 5 Assumes that $t_{\text{RCD}} \geq t_{\text{RCD}} (\text{max.})$.
- 6 Measured with a load equivalent to 2 TTL loads and 100 pF.
- 7 Operation within the $t_{\text{RCD}} (\text{max})$ limit insures that $t_{\text{RAC}} (\text{max})$ can be met. $t_{\text{RCD}} (\text{max})$ is specified as a reference point only; if t_{RCD} is greater than the specified $t_{\text{RCD}} (\text{max})$ limit, then access time is controlled exclusively by t_{CAC} .
- 8 $t_{\text{RCD}} (\text{min}) = t_{\text{RAH}} (\text{min}) + 2t_T$ ($t_T = 5 \text{ ns}$) + $t_{\text{ASC}} (\text{min})$.
- 9 Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.
- 10 t_{WCS} and t_{CWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{\text{WCS}} \geq t_{\text{WCS}} (\text{min})$, the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout entire cycle. If $t_{\text{CWD}} \geq t_{\text{CWD}} (\text{min})$ the cycle is a read-write cycle and data out will contain data read from the selected cell. If neither of the above sets of conditions is satisfied the condition of the data out is indeterminate.
- 11 Test mode cycle only.

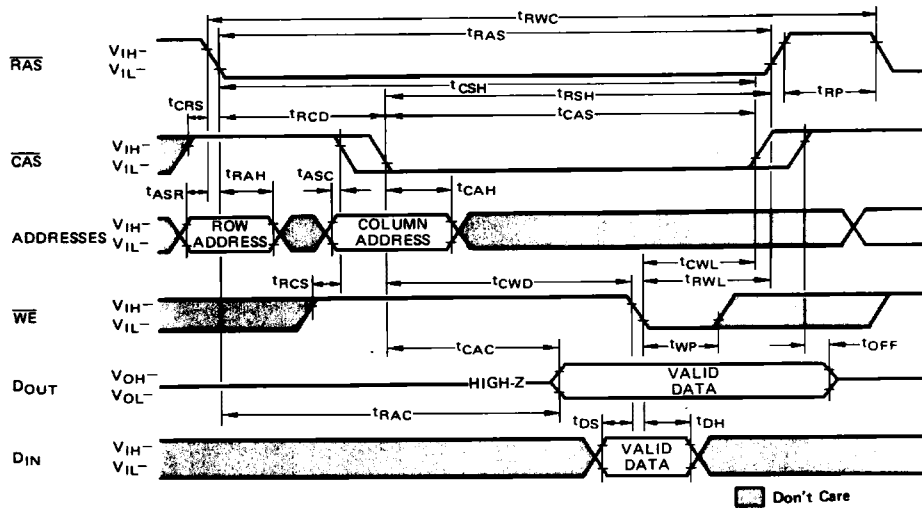
Read Cycle



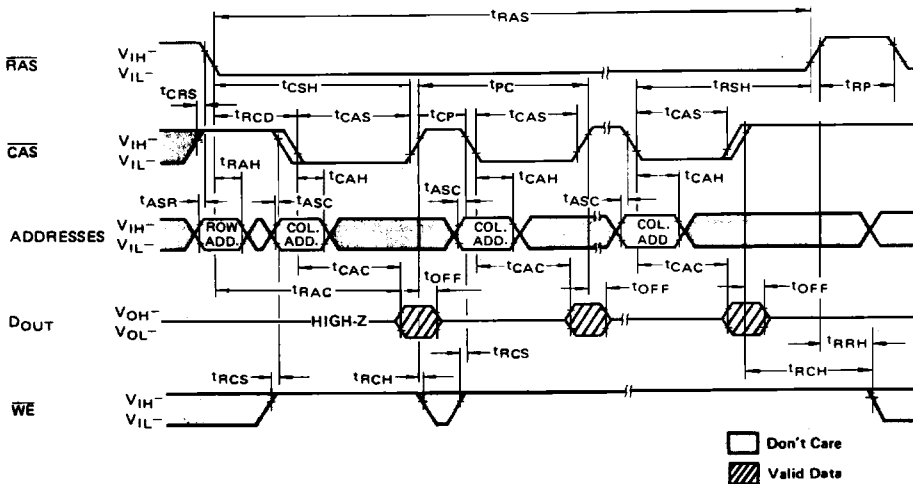
Write Cycle (Early Write)

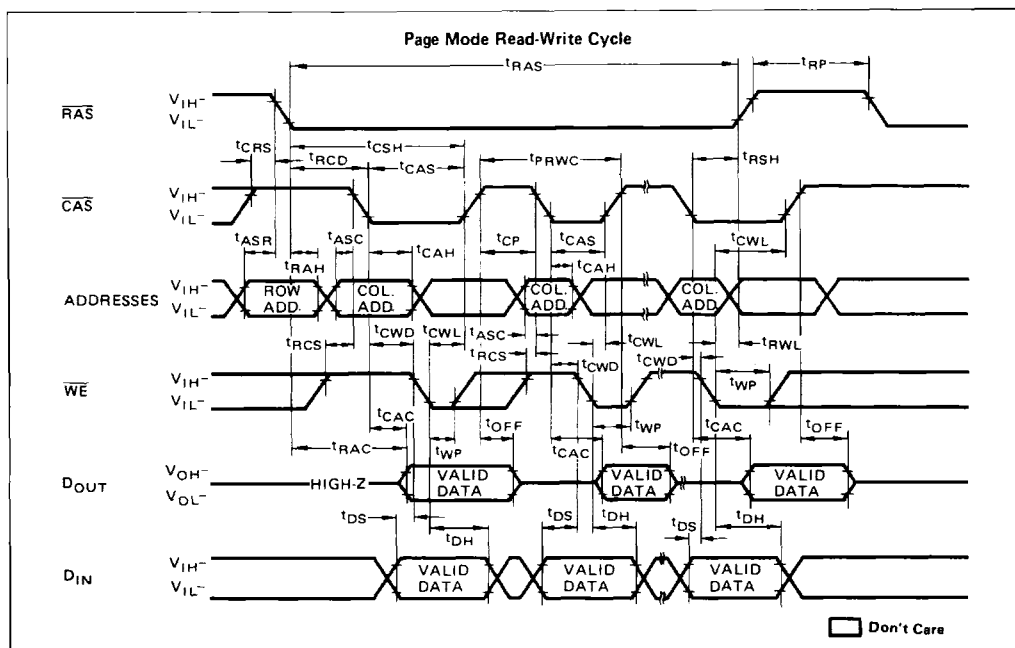


Read-Write/Read-Modify-Write Cycle



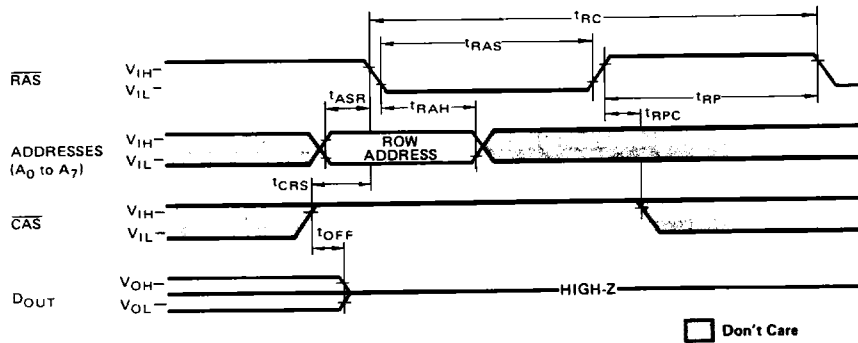
Page Mode Read Cycle





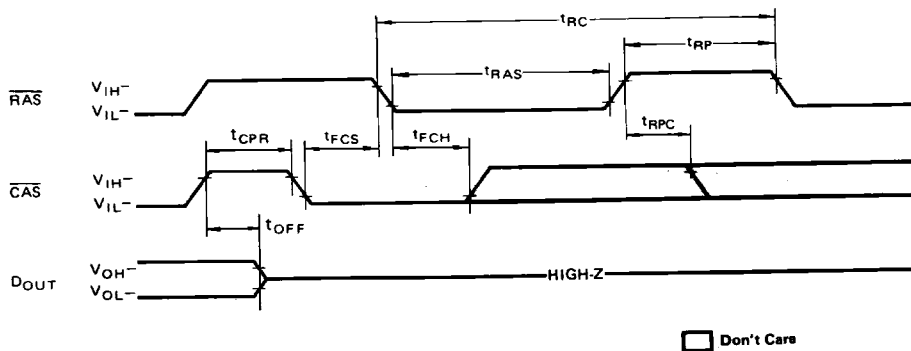
RAS-only Refresh cycle

NOTE: $\overline{WE}$, D_{IN} = Don't care, $A_8 = V_{IH}$ or V_{IL}

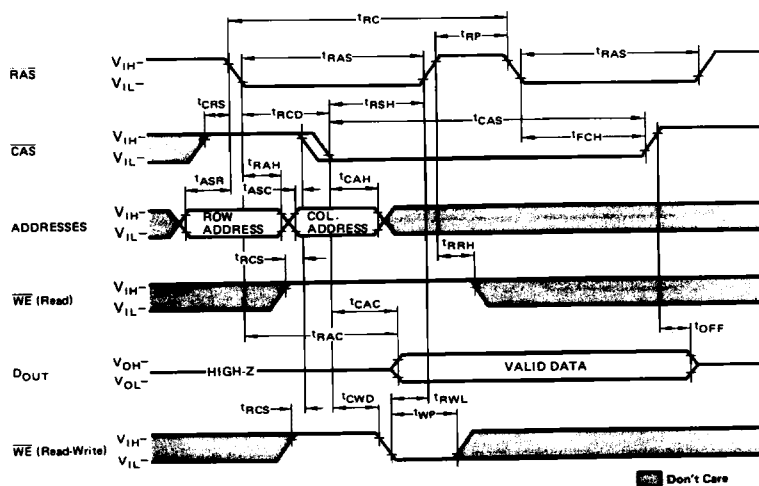


CAS-before-RAS Refresh Cycle

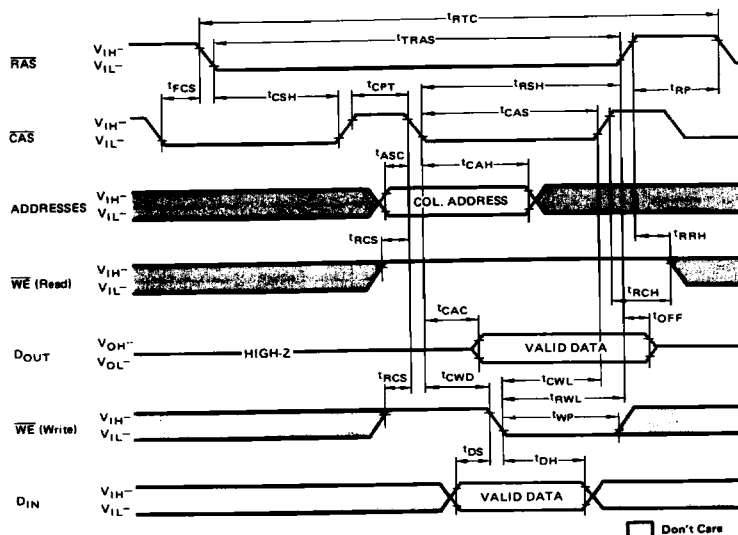
NOTE: Address, $\overline{WE}$, D_{IN} = Don't care



Hidden Refresh Cycle



CAS-before-RAS Refresh Counter Test Cycle



DESCRIPTION

Simple Timing Requirement

The MB 81256 has improved circuitry that eases timing requirements for high speed access operations. The MB 81256 can operate under the condition of $t_{RCD}(\text{max}) = t_{CAC}$ thus providing optimal timing for address multiplexing. In addition, the MB 81256 has the minimal hold time of Address (t_{CAH}), $\overline{WE}$ (t_{WCH}) and D_{IN} (t_{DH}). The MB 81256 provides higher throughput in inter-leaved memory system applications. Fujitsu has made timing requirements that are referenced to RAS nonrestrictive and deleted them from the data sheet, these include t_{AR} , t_{WCR} , t_{DHR} and t_{RWD} . As a result, the hold times of the Column Address, D_{IN} and $\overline{WE}$ as well as t_{CWD} ($\overline{CAS}$ to $\overline{WE}$ Delay) are not restricted by t_{RCD} .

Address Inputs:

A total of eighteen binary input address bits are required to decode any 1 of 262,144 cell locations within the MB 81256. Nine row-address bits are established on the input pins (A_0 to A_8) and are latched with the Row Address Strobe ($\overline{RAS}$). Nine column-address bits are established on the input pins and are latched with the Column Address Strobe ($\overline{CAS}$). All row addresses must be stable on or before the falling edge of $\overline{RAS}$. $\overline{CAS}$ is internally inhibited (or "gated") by $\overline{RAS}$ to permit triggering of $\overline{CAS}$ as soon as the Row Address Hold Time (t_{RAH}) specification has been satisfied and the address inputs have been changed from row-addresses to column-address.

Write Enable:

The read mode or write mode is selected with the $\overline{WE}$ input. A high on $\overline{WE}$ selects read mode; low selects write mode. The data input is disable when read mode is selected.

Data input:

Data is written into the MB 81256 during a write or read-write cycle. The later falling edge of $\overline{WE}$ or $\overline{CAS}$ is a strobe for the Data In (D_{IN}) register. In a write cycle, if $\overline{WE}$ is brought low before

$\overline{CAS}$, D_{IN} is strobed by $\overline{CAS}$, and the set-up and hold times are referenced to $\overline{CAS}$. In a read-write cycle, $\overline{WE}$ can be delayed after $\overline{CAS}$ has been low and $\overline{CAS}$ to $\overline{WE}$ Delay Time (t_{CWD}) has been satisfied. Thus D_{IN} is strobed by $\overline{WE}$, and set-up and hold times are referenced to $\overline{WE}$.

Data Output:

The output buffer is three-state TTL compatible with a fan-out of two standard TTL loads. Data out is the same polarity as data-in. The output is in a high impedance state until $\overline{CAS}$ is brought low. In a read cycle, or read-write cycle, the output is valid after t_{RAC} from transition of $\overline{RAS}$ when $t_{RCD}(\text{max})$ is satisfied, or after t_{CAC} from transition of $\overline{CAS}$ when the transition occurs after $t_{RCD}(\text{max})$. Data remain valid until $\overline{CAS}$ is returned to a high level. In a write cycle the identical sequence occurs, but data is not valid.

Fast Read-While-Write cycle

The MB 81256 has a fast read while write cycle which is achieved by precise control of the three-state output buffer as well as by the simplified timings described in the previous section. The output buffer is controlled by the state of $\overline{WE}$ when $\overline{CAS}$ goes low. When $\overline{WE}$ is low during $\overline{CAS}$ transition to low, the MB 81256 goes into the early write mode in which the output floats and the common I/O bus can be used on the system level. Whereas, when $\overline{WE}$ goes low after t_{CWD} following $\overline{CAS}$ transition to low, the MB 81256 goes into the delayed write mode. The output then contains the data from the cell selected and the data from D_{IN} is written into the cell selected. Therefore, a very fast read write cycle ($t_{RWC} = t_{RC}$) is possible with the MB 81256.

Page Mode:

Page-mode operation permits strobing the row-address into the MB 81256 while maintaining $\overline{RAS}$ at a low throughout all successive memory operations in which the row-address doesn't change. Thus the power dissipated by the

falling edge of $\overline{RAS}$ is saved. Access and cycle times are decreased because the time normally required to strobe a new row address is eliminated.

Refresh:

Refresh of the dynamic memory cells is accomplished by performing a memory cycle at each of the 256 row-addresses (A_0 to A_7) at least every 4ms. The MB 81256 offers the following 3 types of refresh.

$\overline{RAS}$ -only Refresh;

$\overline{RAS}$ -only refresh avoids any output during refresh because the output buffer is in the high impedance state unless $\overline{CAS}$ is brought low. Strobing each of 256 row-addresses (A_0 to A_7) with $\overline{RAS}$ will cause all bits in each row to be refreshed. Further $\overline{RAS}$ -only refresh results in a substantial reduction in power dissipation. During $\overline{RAS}$ -only refresh cycle, either V_{IH} or V_{IL} is permitted to A_8 .

$\overline{CAS}$ -before- $\overline{RAS}$ Refresh;

$\overline{CAS}$ -before- $\overline{RAS}$ refreshing available on the MB 81256 offers an alternate refresh method. If $\overline{CAS}$ is held "low" for the specified period (t_{FCS}) before $\overline{RAS}$ goes to "low", on-chip refresh control clock generators and the refresh address counter are enabled, and an internal refresh operation takes place. After the refresh operation is performed, the refresh address counter is automatically incremented in preparation for the next $\overline{CAS}$ -before- $\overline{RAS}$ refresh operation.

Hidden Refresh;

A hidden refresh cycle may takes place while maintaining the latest valid data at the output by extending $\overline{CAS}$ active time.

For the MB 81256 a hidden refresh is a $\overline{CAS}$ -before- $\overline{RAS}$ refresh cycle. The internal refresh address counters provide the refresh addresses, as in a normal $\overline{CAS}$ -before- $\overline{RAS}$ refresh cycle.

$\overline{CAS}$ -before- $\overline{RAS}$ Refresh Counter Test Cycle:

A special timing sequence using $\overline{CAS}$

before- $\overline{\text{RAS}}$ counter test cycle provides a convenient method of verifying the functionality of the $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh activated circuitry.

After the $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh operation, if $\overline{\text{CAS}}$ goes to high and then goes to low again while $\overline{\text{RAS}}$ is held low, the read and write operations are enabled.

This is shown in the $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ counter test cycle timing diagram. A memory cell address (consisting of a row address (9 bits) and column address (9 bits) to be accessed can be defined as follows:

*A ROW ADDRESS – Bits A_0 to A_7

are defined by the refresh counter.

The bit A_8 is set high internally.

*A COLUMN ADDRESS – All the bits A_0 to A_8 are defined by latching levels on A_0 to A_8 at the second falling edge of $\overline{\text{CAS}}$.

Suggested $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Counter Test Procedure

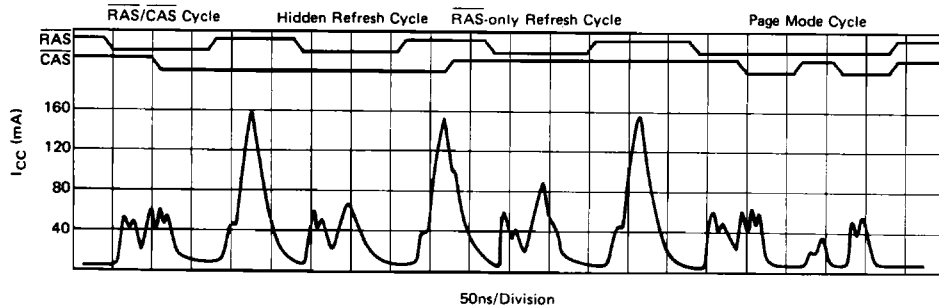
The timing as shown in the $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Counter Test cycles is used for the following operations:

- (1) Initialize the internal refresh address counter by using eight $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycles.
- (2) Throughout the test, use the same

column address, and keep RA8 high.

- (3) Write "low" to all 256 row address on the same column address by using normal early write cycles.
- (4) Read "low" written in step 3) and check, and simultaneously write "high" to the same address by using internal refresh counter test read-write cycles. This step is repeated 256 times, with the addresses being generated by internal refresh address counter.
- (5) Read "high" written in step 4) and check by using normal read cycle for all 256 locations.
- (6) Complement the test pattern and repeat step 3), 4) and 5).

Fig. 2 – CURRENT WAVEFORM ($V_{CC}=5.5V$, $T_A = 25^\circ C$)



TYPICAL CHARACTERISTICS CURVES

Fig. 3 – NORMALIZED ACCESS TIME
vs SUPPLY VOLTAGE

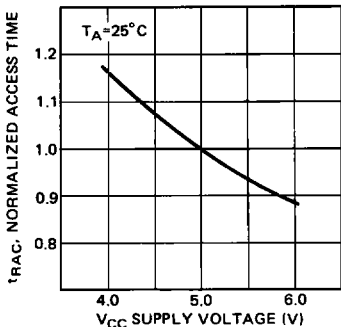


Fig. 4 – NORMALIZED ACCESS TIME
vs AMBIENT TEMPERATURE

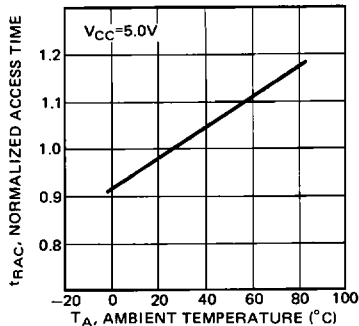


Fig. 5 – OPERATING CURRENT
vs CYCLE RATE

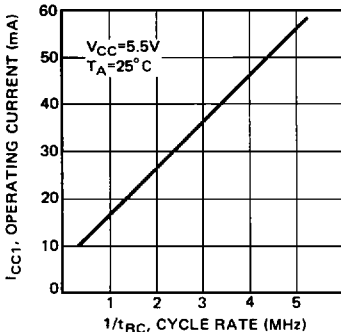


Fig. 6 – OPERATING CURRENT
vs SUPPLY VOLTAGE

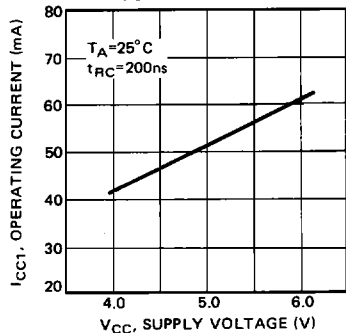


Fig. 7 – OPERATING CURRENT
vs AMBIENT TEMPERATURE

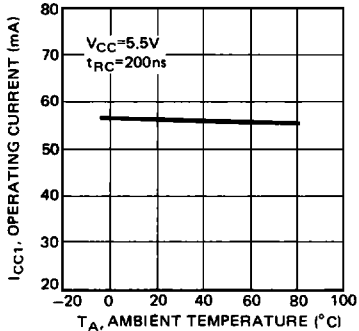


Fig. 8 – STANDBY CURRENT
vs SUPPLY VOLTAGE

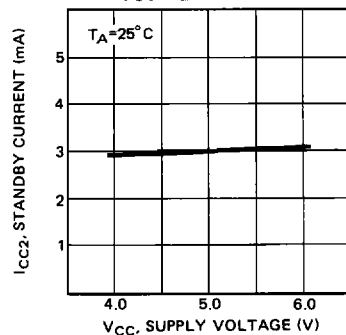


Fig. 9 – STANDBY CURRENT
vs AMBIENT TEMPERATURE

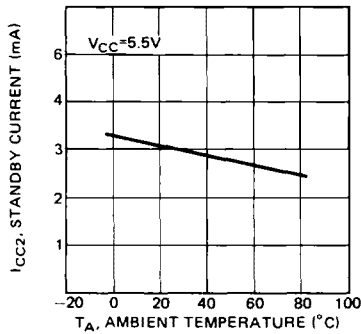


Fig. 10 – REFRESH CURRENT 1
vs CYCLE RATE

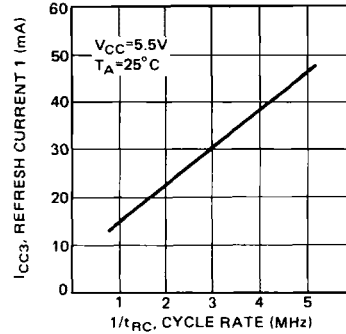


Fig. 11 – REFRESH CURRENT 1
vs SUPPLY VOLTAGE

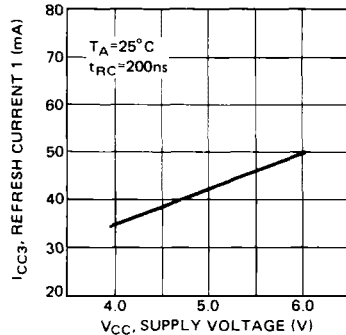


Fig. 12 – PAGE MODE CURRENT
vs CYCLE RATE

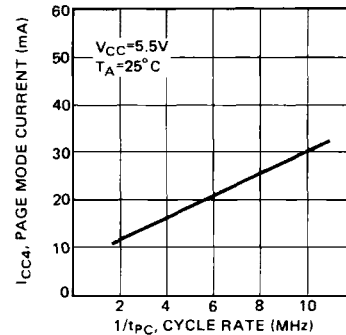


Fig. 13 – PAGE MODE CURRENT
vs SUPPLY VOLTAGE

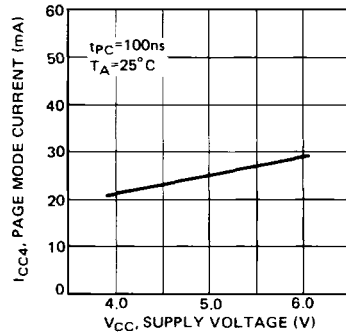


Fig. 14 – REFRESH CURRENT 2
vs CYCLE RATE

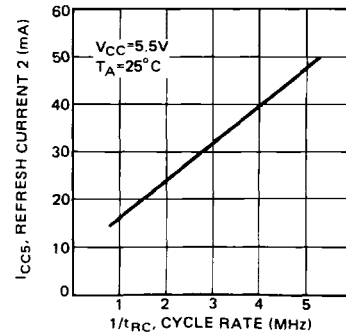


Fig. 15 — REFRESH CURRENT 2
vs SUPPLY VOLTAGE

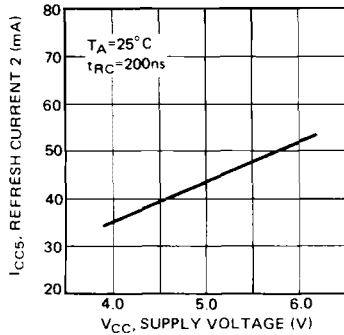


Fig. 16 — ADDRESS AND DATA INPUT
VOLTAGE vs SUPPLY VOLTAGE

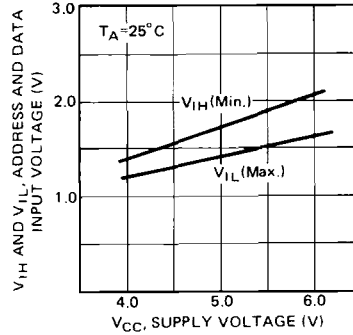


Fig. 17 — ADDRESS AND DATA INPUT
VOLTAGE vs AMBIENT TEMPERATURE

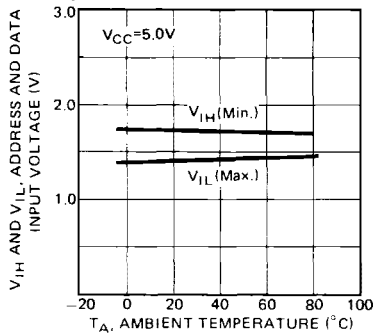


Fig. 18 — RAS, CAS AND WE INPUT
VOLTAGE vs SUPPLY VOLTAGE

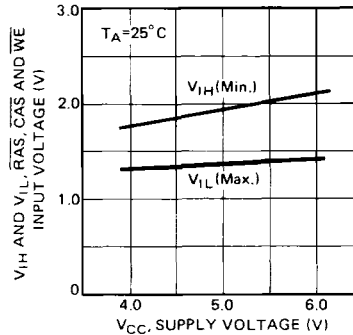


Fig. 19 — RAS, CAS AND WE INPUT
VOLTAGE vs AMBIENT TEMPERATURE

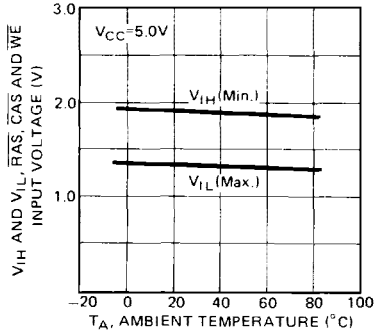


Fig. 20 — ACCESS TIME vs LOAD
CAPACITANCE

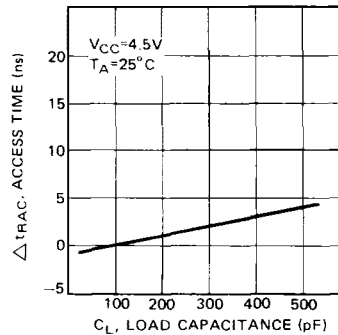


Fig. 21 – OUTPUT CURRENT
vs OUTPUT VOLTAGE

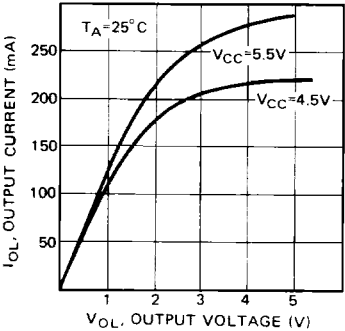


Fig. 22 – OUTPUT CURRENT
vs OUTPUT VOLTAGE

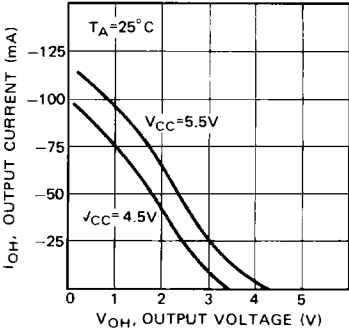


Fig. 23 – CURRENT WAVEFORM
DURING POWER UP

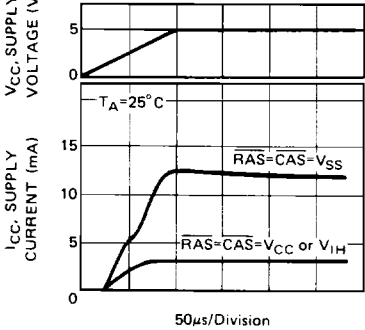
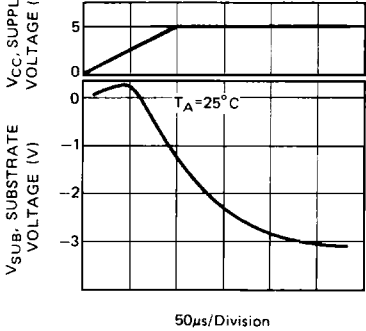
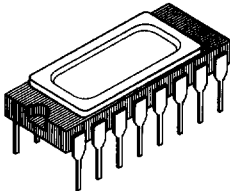


Fig. 24 – SUBSTRATE VOLTAGE
DURING POWER UP

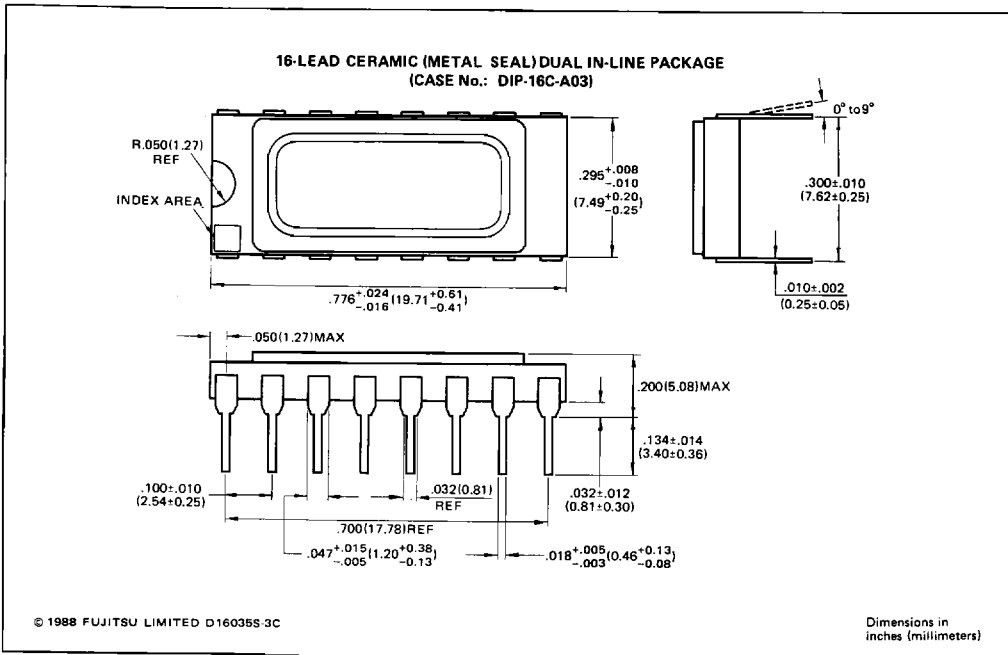


PACKAGE DIMENSIONS

Standard 16-pin Ceramic DIP (Suffix: -C)



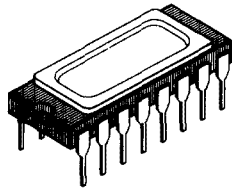
DIP-16C-A03



MB81256-10
MB81256-12
MB81256-15

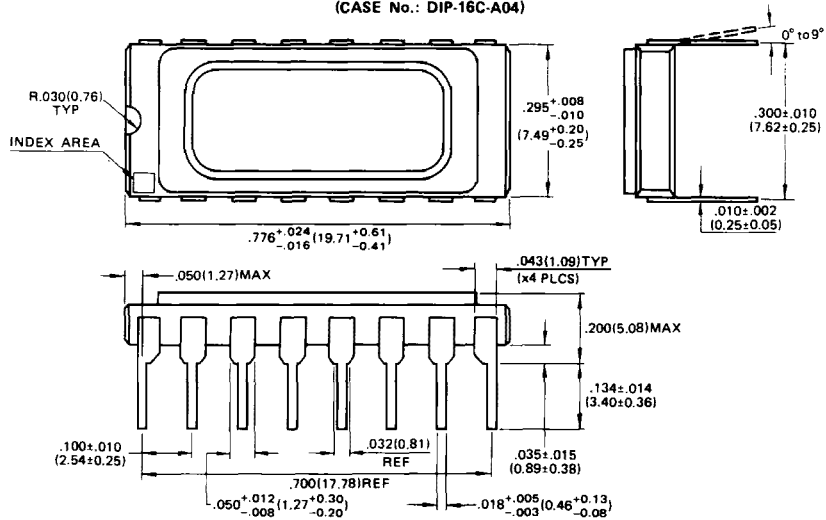
PACKAGE DIMENSIONS

Standard 16-pin Ceramic DIP (Suffix: -C)



DIP-16C-A04

16-LEAD CERAMIC (METAL SEAL) DUAL IN-LINE PACKAGE (CASE No.: DIP-16C-A04)

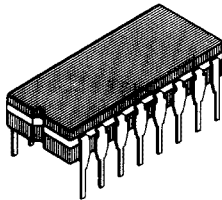


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Dimensions in
inches (millimeters)

PACKAGE DIMENSIONS

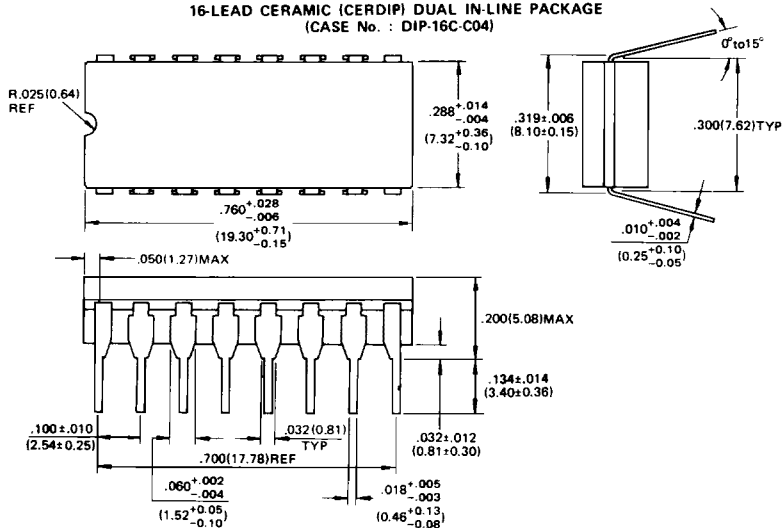
Standard 16-pin Ceramic DIP (Suffix: -Z)



DIP-16C-C04

1

16-LEAD CERAMIC (CERDIP) DUAL IN-LINE PACKAGE (CASE No. : DIP-16C-C04)



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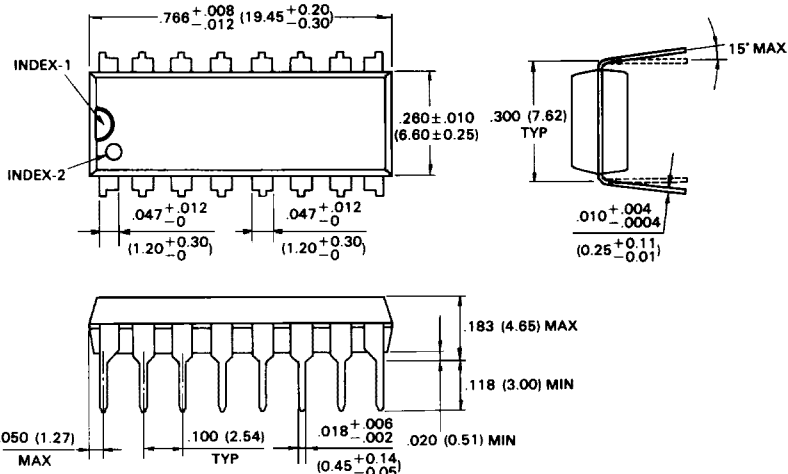
Dimensions in
inches (millimeters)

MB81256-10
MB81256-12
MB81256-15

PACKAGE DIMENSIONS

Standard 16-pin Plastic DIP (Suffix: -P)

16-LEAD PLASTIC DUAL IN-LINE PACKAGE (CASE No.: DIP-16P-M03)



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Dimensions in
inches (millimeters)

Standard 18-pin Plastic LCC (Suffix: -PD)

18-LEAD PLASTIC LEADED CHIP CARRIER (CASE No.: LCC-18P-M04)

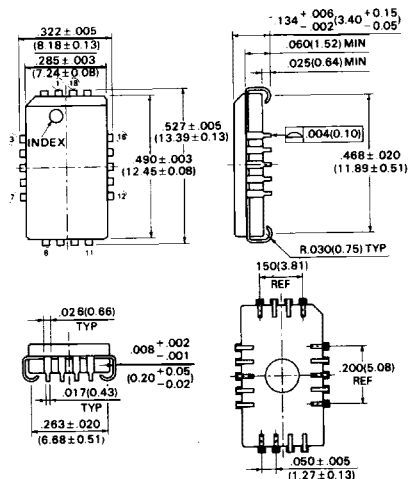


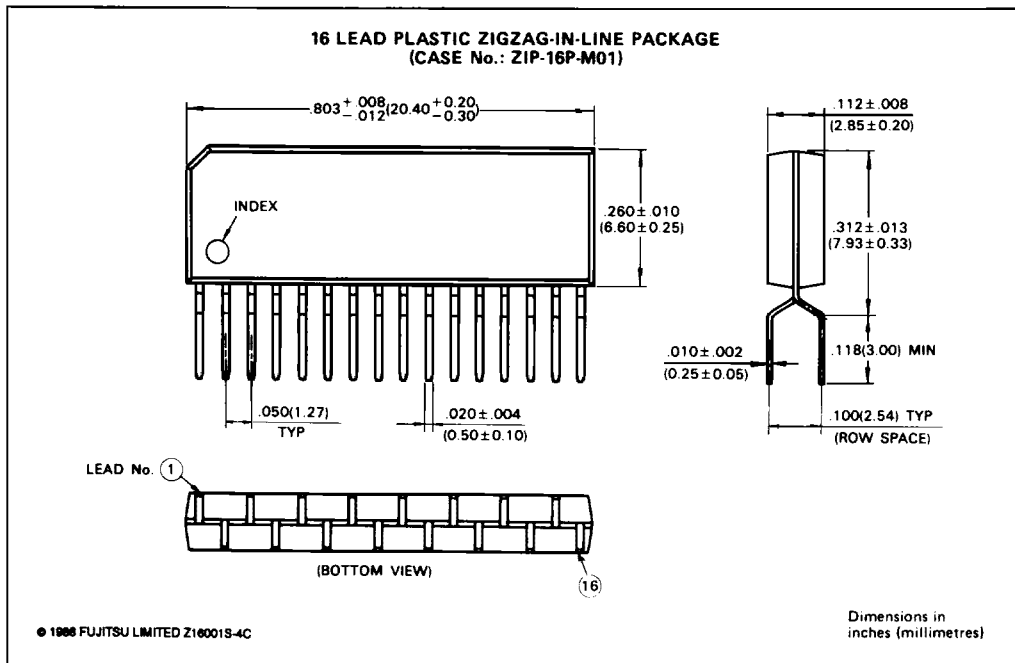
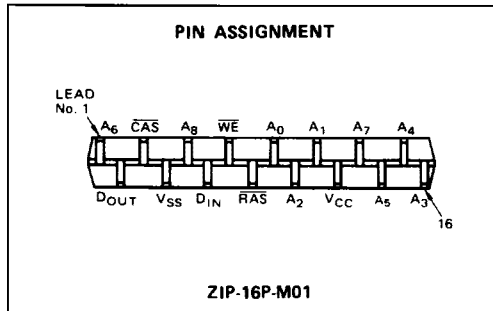
Fig. LEAD No.

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Dimensions in
inches (millimeters)

PACKAGE DIMENSIONS

Standard 16-pin Plastic ZIP (Suffix: -PSZ)

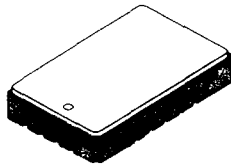


MB81256-10
MB81256-12
MB81256-15

PACKAGE DIMENSIONS

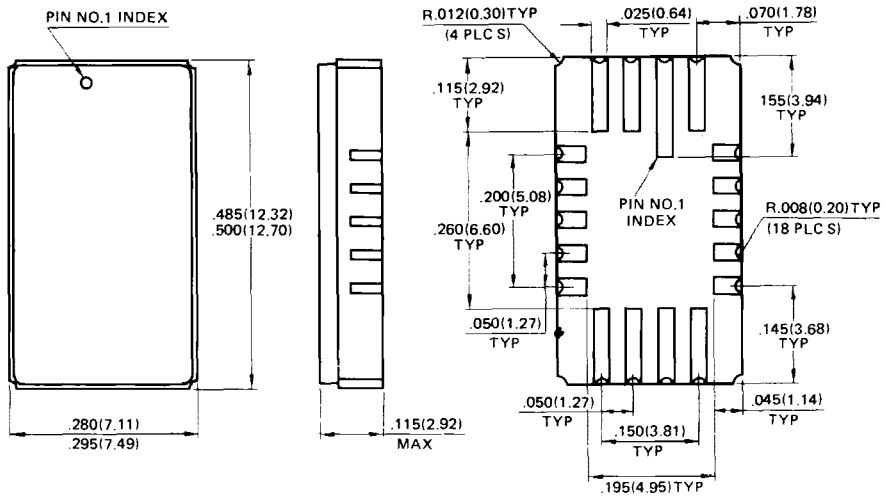
Standard 18-pad Ceramic LCC (Suffix: -TV)

1



LCC-18C-F04

18-PAD CERAMIC (FRIT SEAL) LEADLESS CHIP CARRIER (CASE No.: LCC-18C-F04)



*Shape of Pin 1 index: Subject to change without notice

Dimension in
inches (millimeters).